

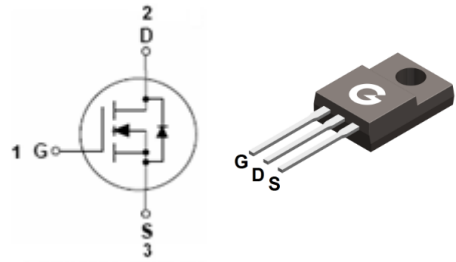
Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

HF

Mechanical Data

- Case: ITO-220AB
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matted-Tin plated; Solderable Per MIL-STD-202, Method 208



ITO-220AB

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL090N12THF	ITO-220AB	50 pcs / Tube	090N12THF

Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	120	V
Gate-to-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$)	I_D	45	A
Continuous Drain Current ($T_C = 100^\circ\text{C}$)		28	A
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_C = 25^\circ\text{C}$)	I_{DM}	180	A
Single Pulse Avalanche Energy ^{*2}	E_{AS}	240	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	35	W
Operating Junction Temperature Range	T_J	$-55 \sim +150$	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	-	3.5	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air	$R_{\theta JA}$	-	-	60	$^\circ\text{C/W}$

Electrical Characteristics (@ $T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	120	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 96V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *1	V _{GS} = 10V, I _D = 50A	-	-	9	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	-	4	V
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	3770	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 60V	-	355	-	
C _{RSS}	Reverse Transfer Capacitance	f = 1MHz	-	17	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time *3	V _{DD} = 50V	-	22	-	ns
t _r	Turn-on Rise Time *3	V _{GS} = 10V	-	18	-	
t _{d(OFF)}	Turn-Off Delay Time *3	R _G = 3Ω	-	49	-	
t _f	Turn-Off Fall Time *3	I _D = 50A	-	19	-	
Q _G	Total Gate-Charge	V _{DD} = 50V	-	56	-	nC
Q _{GS}	Gate to Source Charge	I _D = 50A	-	12	-	
Q _{GD}	Gate to Drain (Miller) Charge	V _{GS} = 10V	-	14	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *1	I _{SD} = 50A, V _{GS} = 0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} = 30A, V _{GS} = 0V	-	66	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt = 100A/μs	-	102	-	nC

Notes:

- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

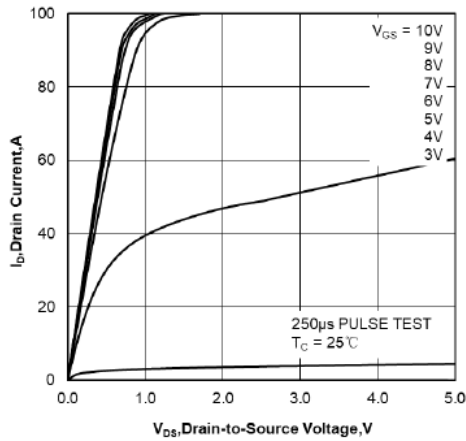


Fig 1 Typical Output Characteristics

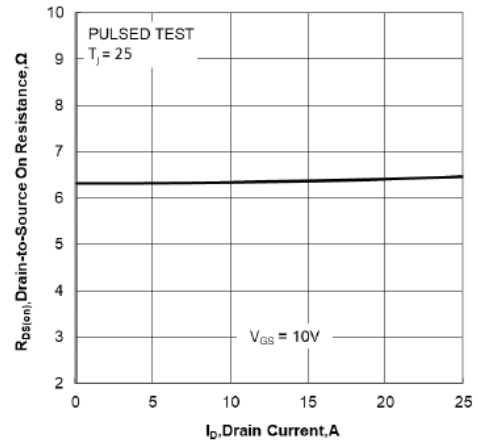


Fig 2 On-Resistance vs. Drain Current
and Gate Voltage

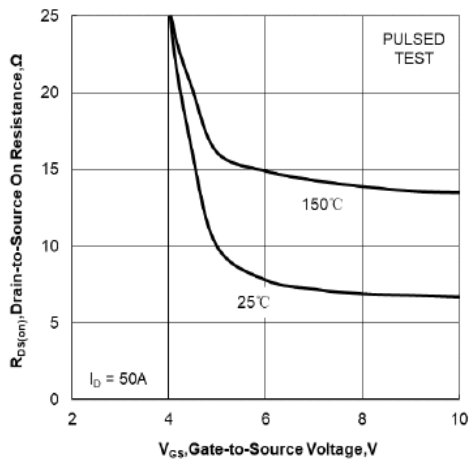


Fig 3 On-Resistance vs. Gate-Source Voltage

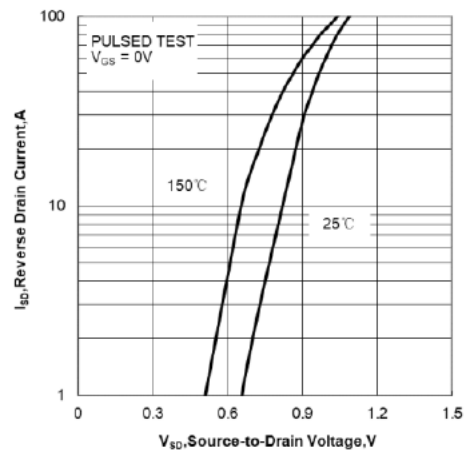


Fig 4 Body-Diode Characteristics

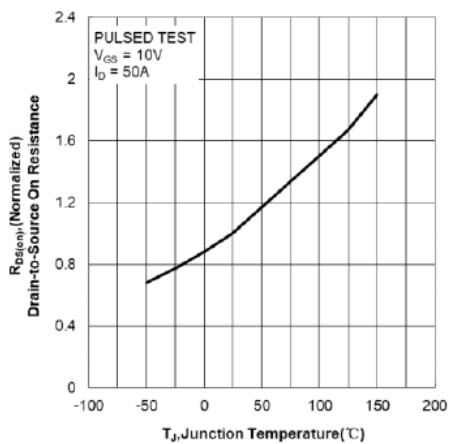


Fig 5 Normalized On-Resistance vs. Junction
Temperature

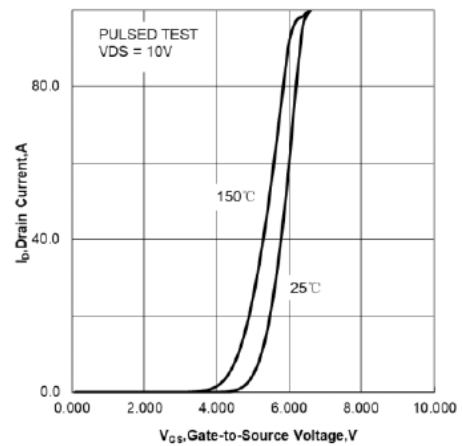


Fig 6 Transfer Characteristics

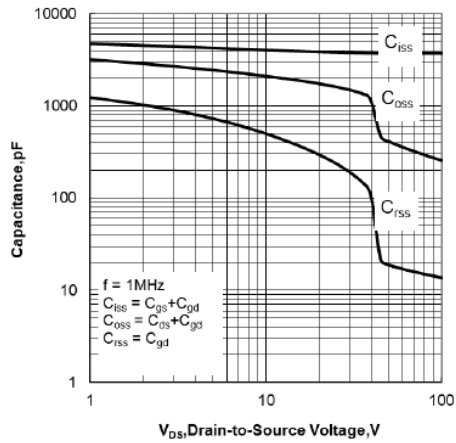


Fig 7 Capacitance Characteristics

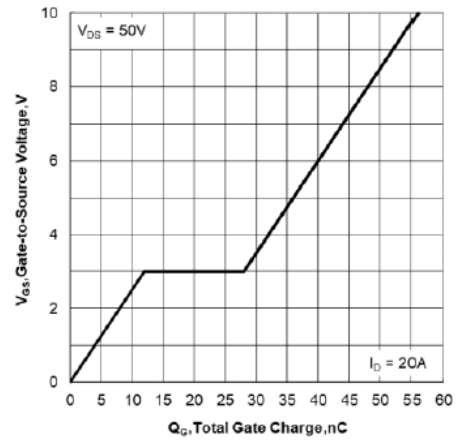


Fig 8 Gate-Charge Characteristics

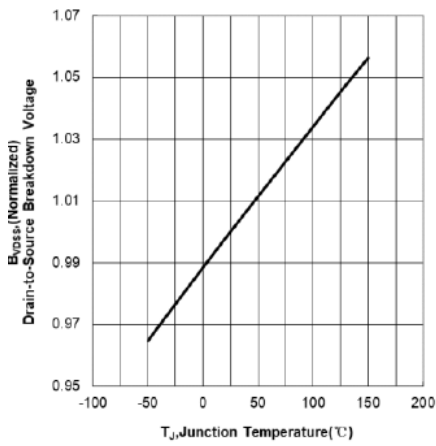
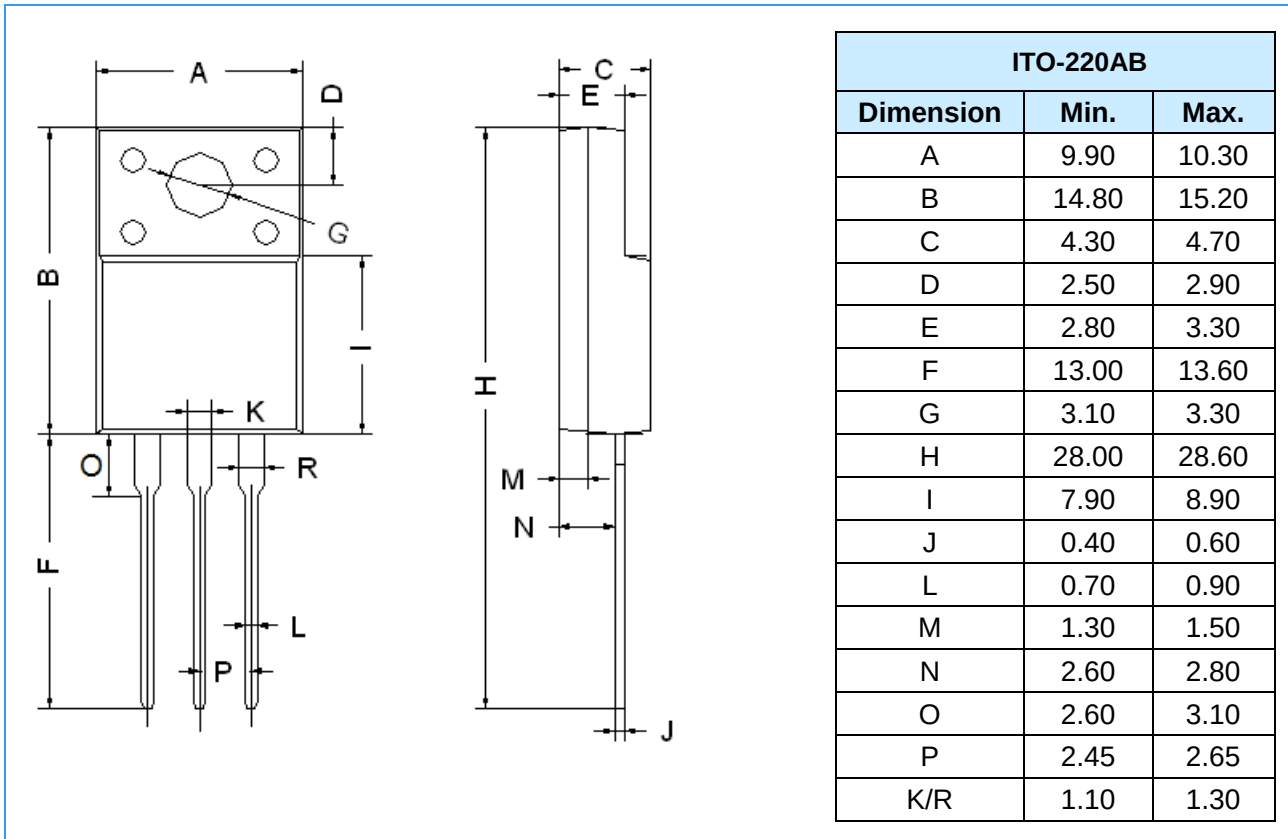


Fig 9 Normalized Breakdown Voltage vs. Junction
Temperature

Package Outline Dimensions (Unit: mm)



IMPORTANT NOTICE

Changzhou Galaxy Century Microelectronics (GME) reserves the right to make changes without further notice to any product information (copyrighted) herein to make corrections, modifications, improvements, or other changes. GME does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others.